NSN 5961-01-151-6001

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View Online at https://aerobasegroup.com/nsn/5961-01-151-6001 **Inclosure Material:** Metal **Overall Length:** 2.637 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-83 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 1.227 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 10.0 peak gate voltage **Current Rating Per Characteristic:** 50.00 amperes forward current, total rms universal **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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